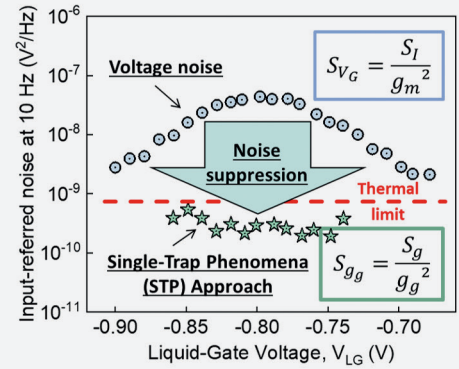
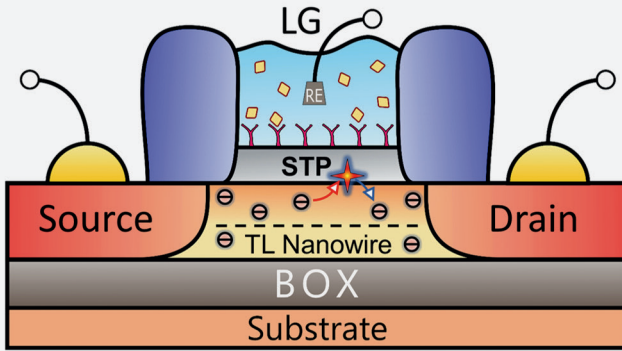




Single-Trap Phenomena in Nanowire Biosensors

Yurii Kutovyi

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